

L Number	Hits	Search Text	DB	Time stamp
-	5921	semiconductor and (etch or etching) and (neutral or neutralize\$3 or neutron)	USPAT	2003/08/15 10:16
-	4506	(semiconductor and (etch or etching) and (neutral or neutralize\$3 or neutron)) and (ion or ionize or ionizing)	USPAT	2003/08/14 14:28
-	50	((semiconductor and (etch or etching) and (neutral or neutralize\$3 or neutron)) and (ion or ionize or ionizing)) and ((reflector or reflecting) with (ion or ionize or ionizing))	USPAT	2003/08/14 15:07
-	8	("3916034" "4471003" "4952843" "5043554" "5082542" "5514229" "5751113" "5767627").PN.	USPAT	2003/08/14 13:31
-	732	((semiconductor and (etch or etching) and (neutral or neutralize\$3 or neutron)) and (ion or ionize or ionizing)) and ((neutral or neutralize\$3 or neutron) with (etch or etching or remove or removing))	USPAT	2003/08/14 14:27
-	522	((semiconductor and (etch or etching) and (neutral or neutralize\$3 or neutron)) and (ion or ionize or ionizing)) and ((neutral or neutralize\$3 or neutron) with (etch or etching or remove or removing)) and ((ion or ionize or ionizing) same (neutral or neutraliz\$3 or neutron))	USPAT	2003/08/14 14:28
-	462	((semiconductor and (etch or etching) and (neutral or neutralize\$3 or neutron)) and (ion or ionize or ionizing)) and ((neutral or neutralize\$3 or neutron) with (etch or etching or remove or removing)) and ((ion or ionize or ionizing) with (neutral or neutraliz\$3 or neutron))	USPAT	2003/08/14 14:28
-	54	((semiconductor and (etch or etching) and (neutral or neutralize\$3 or neutron)) and (ion or ionize or ionizing)) and ((neutral or neutralize\$3 or neutron) with (etch or etching or remove or removing)) and ((ion or ionize or ionizing) with (neutral or neutraliz\$3 or neutron)) and (reflector or reflecting or reflect)	USPAT	2003/08/15 10:19
-	50	((semiconductor and (etch or etching) and (neutral or neutralize\$3 or neutron)) and (ion or ionize or ionizing)) and ((neutral or neutralize\$3 or neutron) with (etch or etching or remove or removing)) and ((ion or ionize or ionizing) with (neutral or neutraliz\$3 or neutron)) and (reflector or reflecting or reflect)) not (((semiconductor and (etch or etching) and (neutral or neutralize\$3 or neutron)) and (ion or ionize or ionizing)) and ((reflector or reflecting) with (ion or ionize or ionizing)))	USPAT	2003/08/14 15:04
-	1	5958157.pn.	USPAT	2003/08/14 15:04
-	8	("3916034" "4471003" "4952843" "5043554" "5082542" "5514229" "5751113" "5767627").PN.	USPAT	2003/08/14 15:04
-	1	5958157.URPN.	USPAT	2003/08/14 15:04
-	1	5958157.URPN.	USPAT	2003/08/14 15:04
-	1	5958157.URPN.	USPAT	2003/08/14 15:04

-	53	((semiconductor and (etch or etching) and (neutral or neutralize\$3 or neutron)) and (ion or ionize or ionizing)) and ((reflector or reflecting or re\$ldirect\$3) with (ion or ionize or ionizing))	USPAT	2003/08/14 15:26
-	3	((semiconductor and (etch or etching) and (neutral or neutralize\$3 or neutron)) and (ion or ionize or ionizing)) and ((reflector or reflecting or re\$ldirect\$3) with (ion or ionize or ionizing))) not (((semiconductor and (etch or etching) and (neutral or neutralize\$3 or neutron)) and (ion or ionize or ionizing)) and ((reflector or reflecting) with (ion or ionize or ionizing)))	USPAT	2003/08/14 15:24
-	1693	((semiconductor and (etch or etching) and (neutral or neutralize\$3 or neutron)) and (ion or ionize or ionizing)) and ((neutral or neutraliz\$3 or neutron) with (ion or ionize or ionizing))	USPAT	2003/08/14 15:26
-	358	((semiconductor and (etch or etching) and (neutral or neutralize\$3 or neutron)) and (ion or ionize or ionizing)) and ((neutral or neutraliz\$3 or neutron) with (ion or ionize or ionizing))) and ((neutral or neutraliz\$3 or neutron) with (etch or etching or remove or removing or etched))	USPAT	2003/08/14 15:27
-	355	((semiconductor and (etch or etching) and (neutral or neutralize\$3 or neutron)) and (ion or ionize or ionizing)) and ((neutral or neutraliz\$3 or neutron) with (ion or ionize or ionizing))) and ((neutral or neutraliz\$3 or neutron) with (etch or etching or remove or removing or etched))) not (((semiconductor and (etch or etching) and (neutral or neutralize\$3 or neutron)) and (ion or ionize or ionizing)) and ((reflector or reflecting or re\$ldirect\$3) with (ion or ionize or ionizing)))	USPAT	2003/08/14 15:27
-	160	((semiconductor and (etch or etching) and (neutral or neutralize\$3 or neutron)) and (ion or ionize or ionizing)) and ((neutral or neutraliz\$3 or neutron) with (ion or ionize or ionizing))) and ((neutral or neutraliz\$3 or neutron) with (etch or etching or remove or removing or etched))) not (((semiconductor and (etch or etching) and (neutral or neutralize\$3 or neutron)) and (ion or ionize or ionizing)) and ((reflector or reflecting or re\$ldirect\$3) with (ion or ionize or ionizing)))) and (beam or beaming)	USPAT	2003/08/15 09:49
-	1	4775789.pn.	USPAT	2003/08/14 18:15
-	7	4775789.URPN.	USPAT	2003/08/14 18:15
-	1	Albridge.in.	USPAT	2003/08/15 09:50
-	7	4775789.URPN.	USPAT	2003/08/15 09:50
-	6191	semiconductor and (etch or etching) and (neutral or neutraliz\$3 or neutron)	USPAT	2003/08/15 10:17
-	2182	(semiconductor and (etch or etching) and (neutral or neutraliz\$3 or neutron)) and ((voltage or power or current) with (reflect\$3 or ion or ionize or ionizing or neutral or netraliz\$3 or neutron))	USPAT	2003/08/15 10:18

-	1021	((semiconductor and (etch or etching) and (neutral or neutraliz\$3 or neutron)) and ((voltage or power or current) with (reflect\$3 or ion or ionize or ionizing or neutral or netraliz\$3 or neutron))) and ((ion or ionize or ionizing) with (neutral or neutraliz\$3 or neutron))	USPAT	2003/08/15 10:19
-	37	((semiconductor and (etch or etching) and (neutral or neutraliz\$3 or neutron)) and ((voltage or power or current) with (reflect\$3 or ion or ionize or ionizing or neutral or netraliz\$3 or neutron))) and ((ion or ionize or ionizing) with (neutral or neutraliz\$3 or neutron)) and ((reflector or reflecting or re\$ldirect\$3) with (ion or ionize or ionizing or neutral or neutraliz%3))	USPAT	2003/08/15 10:20
-	11	4662977.URPN.	USPAT	2003/08/15 10:58